

Amendments to the Claims

1-5. (Cancel)

6-11. (Cancelled)

12. (Currently amended) A method for manufacturing an electronic device, ~~comprising;~~ said method comprising:

electroless plating an electronic device having an embedded interconnect structure with an electroless Ni-B plating liquid to form a protective layer of a Ni-B alloy film having a thickness of 10 to 100 nm selectively on a surface of an interconnect of said electronic device;

wherein said electroless Ni-B plating liquid comprises nickel ions, a complex agent for nickel ions, a reducing agent for nickel ions, and ammonium ions (NH_4^+).

13. (Original) The method according to claim 12, wherein said Ni-B alloy film has an FCC crystalline structure.

14. (Original) The method according to claim 12, wherein said Ni-B alloy film has a boron content within the range from 0.01 at% to 10 at%.

15-16. (Cancel)

17. (New) The method according to claim 12, wherein said ammonium ions are prepared from ammonia water.

18. (New) The method according to claim 12, wherein a pH of said electroless Ni-B plating liquid is adjusted within the range from 8 to 12.

19. (New) The method according to claim 12, wherein a temperature of said electroless Ni-B plating liquid is adjusted within the range from 50 °C to 90 °C.